



BTA2008-1000D

3Q Hi-Com Triac

18 March 2013

Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a SOT54 (TO-92) plastic package. This "series D" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers and logic ICs including microcontrollers.

2. Features and benefits

- 3Q technology for improved noise immunity
- Direct gate triggering from low power drivers and logic ICs
- High commutation capability with very sensitive gate
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- Very sensitive gate for easy logic level triggering

3. Applications

- Low power motor controls
- Small inductive loads e.g. solenoids, door locks, water valves
- Small loads in large white goods

4. Quick reference data

Table 1. Quick reference data

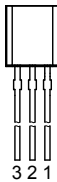
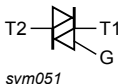
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	1000	V
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{J}(\text{init})} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	-	9	A
T_{J}	junction temperature		-	-	125	$^{\circ}\text{C}$
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{lead}} \leq 70\text{ }^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	0.8	A
Static characteristics						
I_{GT}	gate trigger current	$V_{\text{D}} = 12\text{ V}$; $I_{\text{T}} = 0.1\text{ A}$; T2+ G+; $T_{\text{J}} = 25\text{ }^{\circ}\text{C}$; Fig. 7	0.25	-	5	mA



Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	0.25	-	5	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	0.25	-	5	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 670\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit	-	150	-	V/ μs
dI_{com}/dt	rate of change of commutating current	$V_D = 400\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $I_{T(RMS)} = 0.8\text{ A}$; $dV_{com}/dt = 1\text{ V}/\mu\text{s}$; gate open circuit	1	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2	 TO-92 (SOT54)	 sym051
2	G	gate		
3	T1	main terminal 1		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA2008-1000D	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54
BTA2008-1000D/L01	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

7. Marking

Table 4. Marking codes

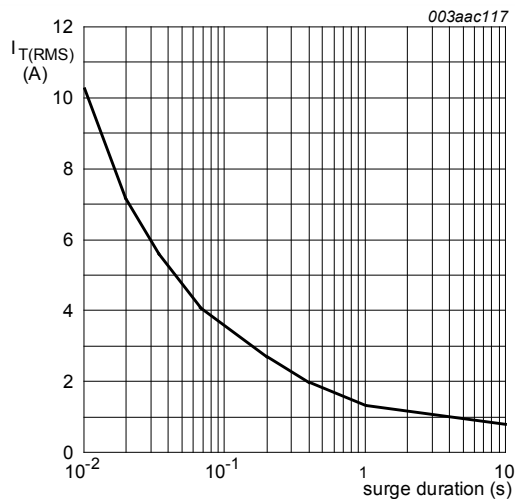
Type number	Marking code
BTA2008-1000D	200810D
BTA2008-1000D/L01	

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	1000	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{lead}} \leq 70\text{ }^{\circ}\text{C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	0.8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	9	A
		full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$; $t_{\text{p}} = 16.7\text{ ms}$	-	9.9	A
I^2t	I^2t for fusing	$t_{\text{p}} = 10\text{ ms}$; sine-wave pulse	-	0.41	A^2s
dl_{T}/dt	rate of rise of on-state current	$I_{\text{T}} = 1.5\text{ A}$; $I_{\text{G}} = 20\text{ mA}$; $dl_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$	-	100	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		-	1	A
P_{GM}	peak gate power		-	2	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period	-	0.1	W
T_{stg}	storage temperature		-40	150	$^{\circ}\text{C}$
T_{j}	junction temperature		-	125	$^{\circ}\text{C}$



$f = 50\text{ Hz}$; $T_{\text{lead}} = 70\text{ }^{\circ}\text{C}$

Fig. 1. RMS on-state current as a function of surge duration; maximum values

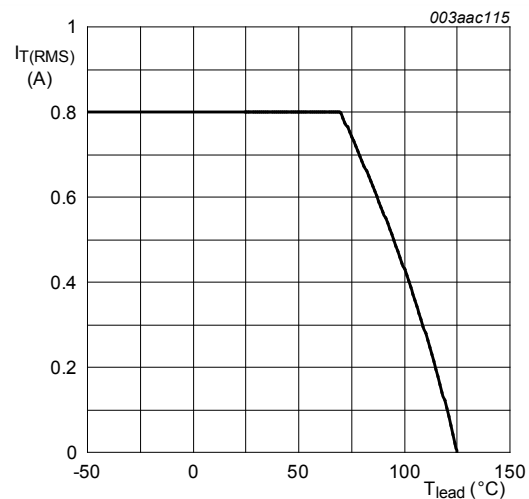


Fig. 2. RMS on-state current as a function of lead temperature; maximum values

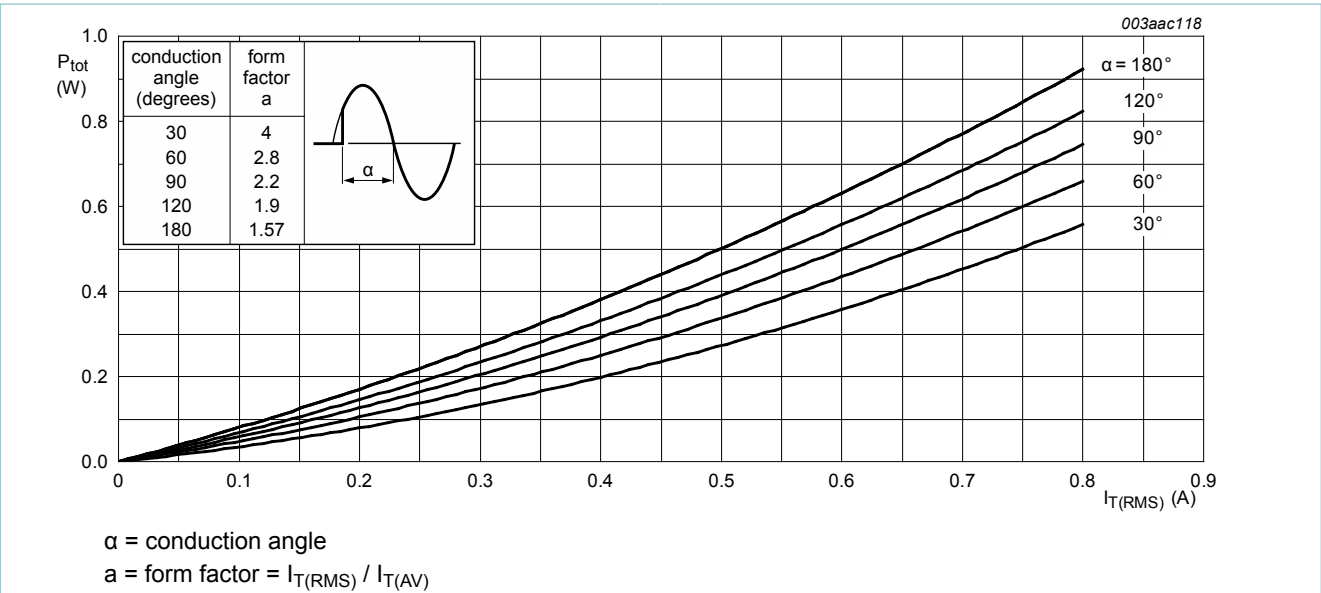


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

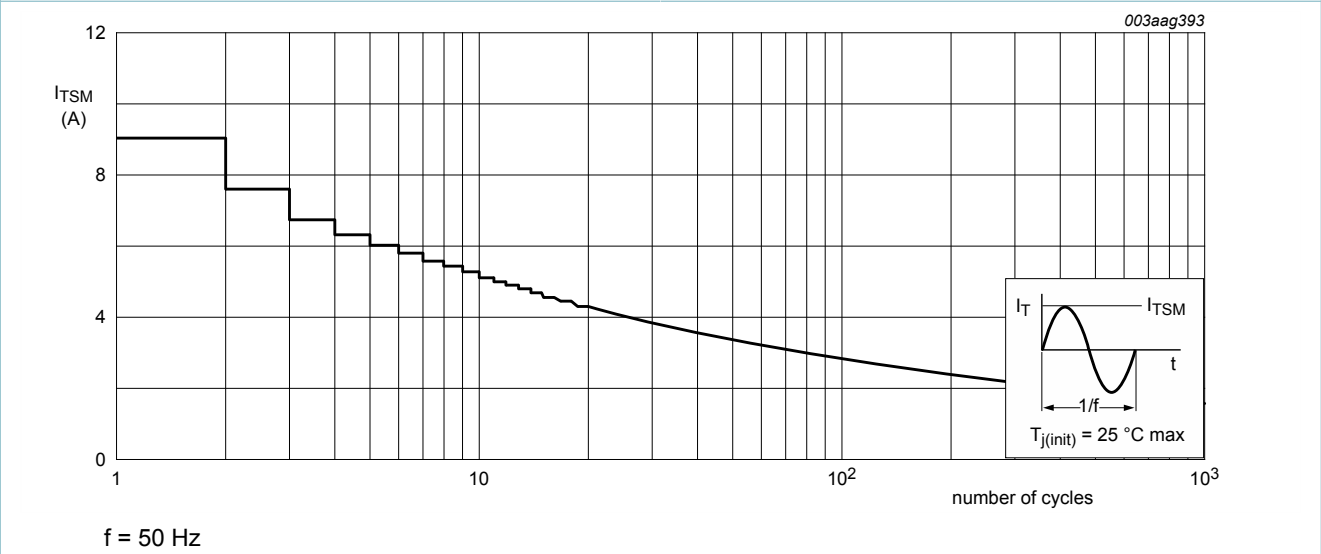
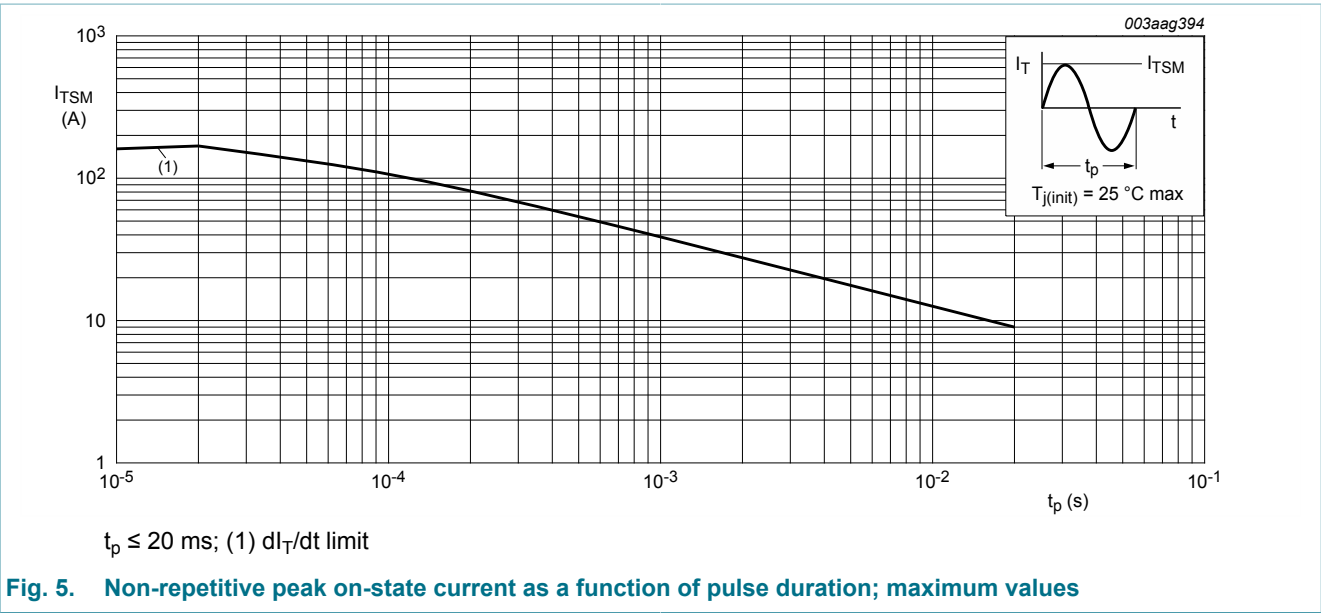


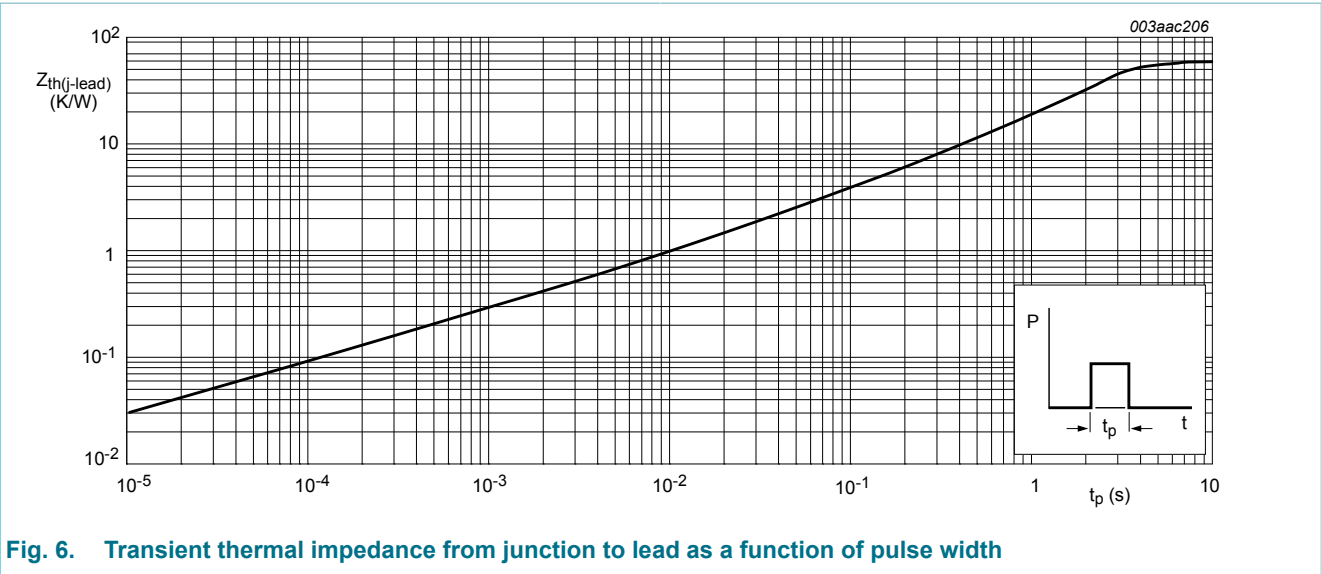
Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



9. Thermal characteristics

Table 6. Thermal characteristics

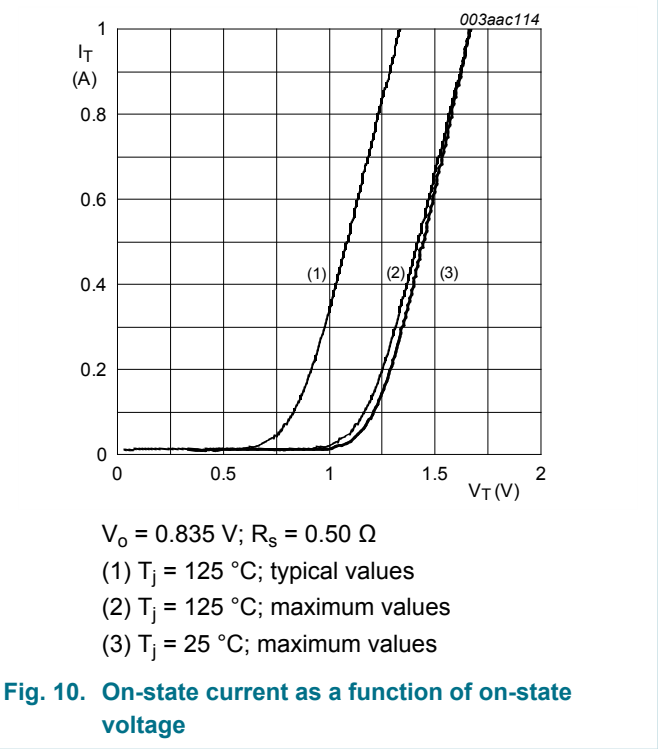
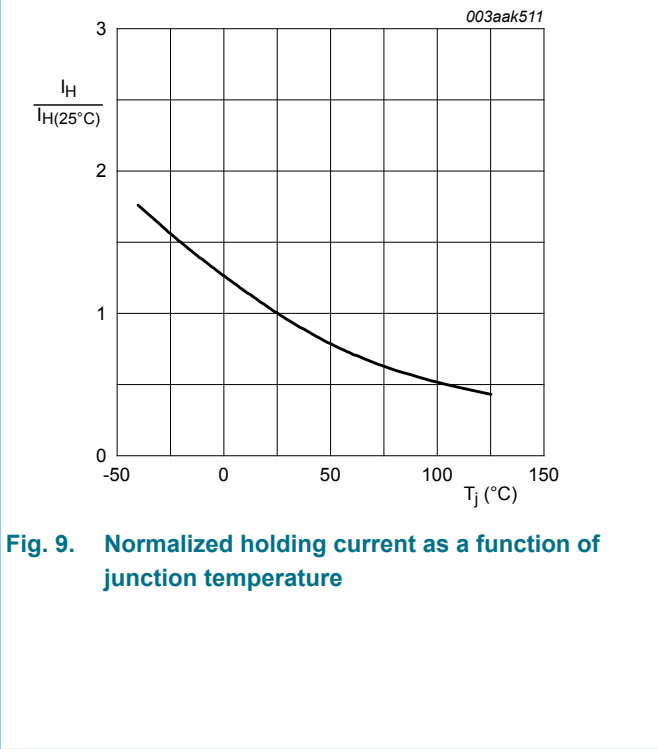
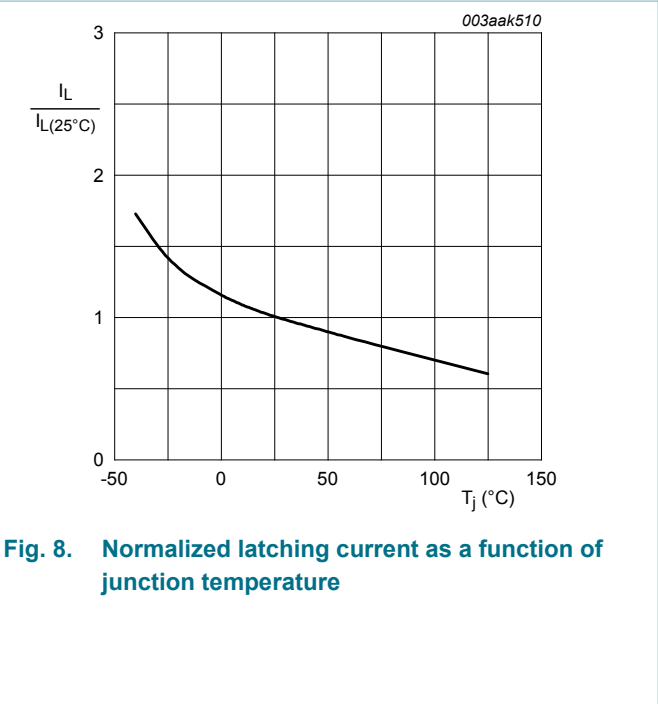
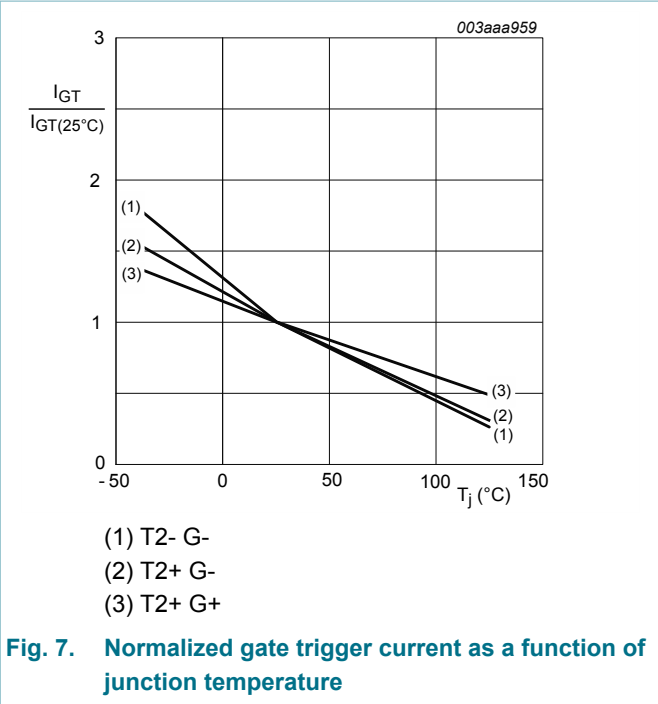
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	full cycle; Fig. 6	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	printed circuit board mounted: lead length = 4 mm	-	150	-	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	0.25	-	5	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	0.25	-	5	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	0.25	-	5	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$; Fig. 8	-	-	10	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 8	-	-	20	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 8	-	-	10	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 9	-	-	10	mA
V_T	on-state voltage	$I_T = 0.85\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 10	-	1.3	1.6	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 11	-	0.85	1	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ }^\circ\text{C}$; Fig. 11	0.2	0.3	-	V
I_D	off-state current	$V_D = 1000\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$	-	0.1	0.5	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 670\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit	-	150	-	V/ μs
dI_{com}/dt	rate of change of commutating current	$V_D = 400\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $I_{T(RMS)} = 0.8\text{ A}$; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$; gate open circuit	0.5	-	-	A/ms
		$V_D = 400\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $I_{T(RMS)} = 0.8\text{ A}$; $dV_{com}/dt = 1\text{ V}/\mu\text{s}$; gate open circuit	1	-	-	A/ms



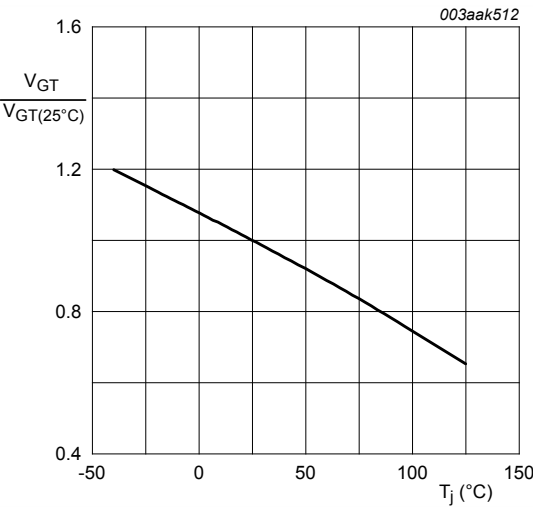


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

11. Package outline

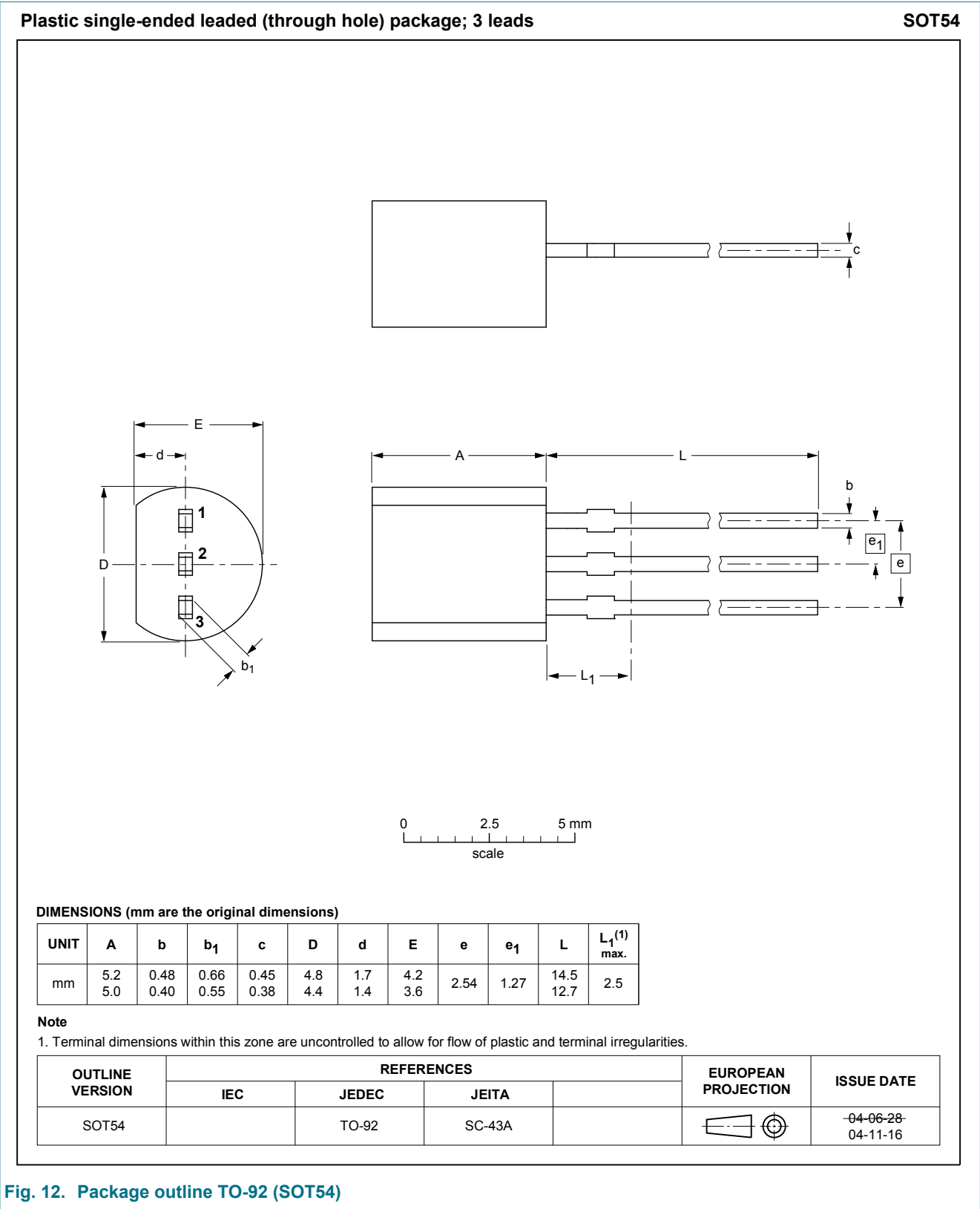


Fig. 12. Package outline TO-92 (SOT54)

12. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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